L Numb r	Hits	Search T xt	DB	Time stamp
160	1	6235600.URPN.	USPAT	2002/09/20 13:55
161	4	("5885877" "5920782" "5972783" "5994175").PN.	USPAT	2002/09/20 13:55
	0	20020076877A1	USPAT;	2002/09/19
'	U	20020076677A1	US-PGPUB;	10:53
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	"20020076877"	USPAT;	2002/09/19
			US-PGPUB;	11:00
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	36	mosfet and (insulator or insulating or	USPAT;	2002/09/19
		dielectric) and (polysilicon or poly-silicon)	US-PGPUB;	11:05
		and liner and spacer and sidewall and	EPO; JPO;	
		(interlevel or inter-level or interlayer or	DERWENT;	
		inter-layer)	IBM_TDB	
-	2	(mosfet and (insulator or insulating or	USPAT;	2002/09/19
		dielectric) and (polysilicon or poly-silicon)	US-PGPUB;	11:05
		and liner and spacer and sidewall and	EPO; JPO;	
		(interlevel or inter-level or interlayer or	DERWENT;	
		inter-layer)) and ((insulator or insulating or	IBM_TDB	
		dielectric) same (polysilicon or poly-silicon)		
		same liner same (spacer or sidewall) same		
		(interlevel or interlayer or inter-level or inter-layer))		
	438	mosfet and (insulator or insulating or	USPAT;	2002/09/19
•	430	dielectric) and (polysilicon or poly-silicon)	US-PGPUB;	11:05
		and oxide and spacer and sidewall and	EPO; JPO;	
		(interlevel or inter-level or interlayer or	DERWENT;	
		inter-layer)	IBM_TDB	
_	61	(mosfet and (insulator or insulating or	USPAT;	2002/09/19
-	01	dielectric) and (polysilicon or poly-silicon)	US-PGPUB;	11:08
		and oxide and spacer and sidewall and	EPO; JPO;	
		(interlevel or inter-level or interlayer or	DERWENT;	
		inter-layer)) and ((insulator or insulating or	IBM_TDB	
		dielectric) same (polysilicon or poly-silicon)		
		same oxide same (spacer or sidewall) same		
		(interlevel or interlayer or inter-level or		
		inter-layer))		
_	9	((mosfet and (insulator or insulating or	USPAT;	2002/09/19
-	J	dielectric) and (polysilicon or poly-silicon)	US-PGPUB;	11:06
		and oxide and spacer and sidewall and	EPO; JPO;	
		(interlevel or inter-level or interlayer or	DERWENT;	
		inter-layer)) and ((insulator rinsulating r	IBM_TDB	
		dielectric) same (p lysilic n or p ly-silicon)		
		sam oxide sam (spacer r sid wall) sam		
		(interl vel or int rlayer r int r-level r		
		inter-lay r))) and liner		

_	9	(((mosf t and (insulator r insulating r	USPAT;	2002/09/19
_		dielectric) and (polysilicon rp ly-silic n)	US-PGPUB;	11:07
		and oxide and spac r and sid wall and	EPO; JP ;	
		(interl v lorint r-lev l rint rlay r r	DERWENT;	
		int r-lay r)) and ((insulat r rinsulating r	IBM_TDB	
			10111_100	
		di I ctric) sam (polysilic n or poly-silic n)		
		same oxide same (spacer or sidewall) same		
		(interlevel or interlayer or inter-level or		
		inter-layer))) and liner) and (liner near10 oxide)		
-	48	(mosfet and (insulator or insulating or	USPAT;	2002/09/19
		dielectric) and (polysilicon or poly-silicon)	US-PGPUB;	11:09
		and oxide and spacer and sidewall and	EPO; JPO;	
		(interlevel or inter-level or interlayer or	DERWENT;	
		inter-layer)) and ((insulator or insulating or	IBM_TDB	
		dielectric) near100 (polysilicon or		
		poly-silicon) near "100" oxide near100		
		(spacer or sidewall) near100 (interlevel or		
		interlayer or inter-level or inter-layer))		
_	10	(mosfet and (insulator or insulating or	USPAT;	2002/09/19
•		dielectric) and (polysilicon or poly-silicon)	US-PGPUB;	11:11
		and oxide and spacer and sidewall and	EPO; JPO;	
		(interlevel or inter-level or interlayer or	DERWENT;	
		•	IBM_TDB	
		inter-layer)) and ((insulator or insulating or	IBIN_IDB	
		dielectric) near50 (polysilicon or		
		poly-silicon) near50 oxide near50 (spacer or		
		sidewall) near50 (interlevel or interlayer or		
		inter-level or inter-layer))		0000/00/40
•	2	(mosfet and (insulator or insulating or	USPAT;	2002/09/19
		dielectric) and (polysilicon or poly-silicon)	US-PGPUB;	11:12
•		and oxide and spacer and sidewall and	EPO; JPO;	
		(interlevel or inter-level or interlayer or	DERWENT;	
		inter-layer)) and (((insulator or insulating or	IBM_TDB	
		dielectric) near30 (polysilicon or		
		poly-silicon) near30 oxide near30 (spacer or		
		sidewall) near30 (interlevel or interlayer or		
		inter-level or inter-layer)) near30 liner)		
-	10	(mosfet and (insulator or insulating or	USPAT;	2002/09/19
		dielectric) and (polysilicon or poly-silicon)	US-PGPUB;	11:12
		and oxide and spacer and sidewall and	EPO; JPO;	
		(interlevel or inter-level or interlayer or	DERWENT;	
		inter-layer)) and ((insulator or insulating or	IBM_TDB	
		dielectric) near30 (polysilicon or	_	
		poly-silicon) near30 oxide near30 (spacer or		
		sidewall) near30 (interlevel or interlayer or		
		inter-level or inter-layer))		1
_	64	((insulator or insulating or dielectric) near30	USPAT;	2002/09/19
-	0-4	(insulator of insulating of dielectric) hearso (polysilicon or poly-silicon) near30 oxide	US-PGPUB;	11:14
		n ar30 (spac r or sid wall) near30	EPO; JPO;	
		(int riev i rint riayer or int r-lev i r	DERWENT;	į
		,	IBM_TDB	
	1	int r-lay r))		L

f	1		T	
-	4	((insulator or insulating r di l ctric) n ar30	USPAT;	2002/09/19
		(p lysilicon r p ly-silic n) n ar30 oxid	US-PGPUB;	11:16
		near30 (spac r or sidewall) n ar30	EPO; JPO;	
		(int rl v lor int rlay r r inter-l v lor	DERWENT;	
		int r-lay r) near30 liner)	IBM_TDB	
-	64	((insulat r or insulating r di l ctric) n ar30	USPAT;	2002/09/19
		(polysilicon or poly-silicon) near30 oxide	US-PGPUB;	11:16
		near30 (spacer or sidewall) near30	EPO; JPO;	
		(interlevel or interlayer or inter-level or	DERWENT;	
		inter-layer))	IBM_TDB	
-	4	(((insulator or insulating or dielectric)	USPAT;	2002/09/19
		near30 (polysilicon or poly-silicon) near30	US-PGPUB;	11:16
		oxide near30 (spacer or sidewall) near30	EPO; JPO;	
		(interlevel or interlayer or inter-level or	DERWENT;	
		inter-layer))) and (oxide near10 liner)	IBM_TDB	
•	4	(((insulator or insulating or dielectric)	USPAT;	2002/09/19
		near30 (polysilicon or poly-silicon) near30	US-PGPUB;	11:16
		oxide near30 (spacer or sidewall) near30	EPO; JPO;	
		(interlevel or interlayer or inter-level or	DERWENT;	
		inter-layer))) and liner	IBM TDB	
-	76	((insulator or insulating or dielectric) near50	USPAT;	2002/09/19
		(polysilicon or poly-silicon) near50 oxide	US-PGPUB;	11:17
		near50 (spacer or sidewall) near50	EPO; JPO;	
		(interlevel or interlayer or inter-level or	DERWENT;	
		inter-layer))	IBM_TDB	
-	4	(((insulator or insulating or dielectric)	USPAT;	2002/09/19
		near50 (polysilicon or poly-silicon) near50	US-PGPUB;	11:17
		oxide near50 (spacer or sidewall) near50	EPO; JPO;	,
		(interlevel or interlayer or inter-level or	DERWENT;	
		inter-layer))) and liner	IBM_TDB	
_	82	((insulator or insulating or dielectric)	_	2002/00/40
	02	near100 (polysilicon or poly-silicon) near100	USPAT; US-PGPUB;	2002/09/19 11:19
		oxide near100 (spacer or sidewall) near100		11:13
		(interlevel or interlayer or inter-level or	EPO; JPO;	
			DERWENT;	
_	4	inter-layer)) (((insulator or insulating or dielectric)	IBM_TDB	2002/00/40
-	*	•	USPAT;	2002/09/19
		near100 (polysilicon or poly-silicon) near100	US-PGPUB;	11:18
		oxide near100 (spacer or sidewall) near100	EPO; JPO;	
		(interlevel or interlayer or inter-level or	DERWENT;	
		inter-layer))) and liner	IBM_TDB	
•	2	(((insulator or insulating or dielectric)	USPAT;	2002/09/19
		near100 (polysilicon or poly-silicon) near100	US-PGPUB;	11:19
		oxide near100 (spacer or sidewall) near100	EPO; JPO;	
		(interlevel or interlayer or inter-level or	DERWENT;	
		inter-layer))) and L-shaped	IBM_TDB	
•	5	(((insulator or insulating or dielectric)	USPAT;	2002/09/19
		near100 (polysilicon or poly-silicon) near100	US-PGPUB;	11:21
		oxide near100 (spacer or sidewall) near100	EPO; JPO;	
		(int rlevel or interlayer or int r-level or	DERWENT;	
		inter-layer))) and (spacer near5 shap d)	IBM_TDB	

	206	L-shaped near spac r	USPAT;	2002/00/40
-	200	L-Shapeu hear spac r	US-PGPUB;	2002/09/19 14:00
			1	14:00
			EPO; JPO;	
			DERWENT;	
1_	0	altair and non-t-ahual ai a	IBM_TDB	2002/20/40
-	•	altair and nan t chnol gi s	USPAT;	2002/09/19
			US-PGPUB;	13:47
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	0	altair and nanotech	USPAT;	2002/09/19
			US-PGPUB;	13:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	227	altair	USPAT;	2002/09/19
			US-PGPUB;	13:49
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	30	altair.asnm.	USPAT;	2002/09/19
1			US-PGPUB;	13:54
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	small near technology near venture near	USPAT;	2002/09/19
		capital	US-PGPUB;	13:55
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1073	harris near harris	USPAT;	2002/09/19
			US-PGPUB;	13:56
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(harris near harris).asnm.	USPAT;	2002/09/19
			US-PGPUB;	13:56
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	54375	harris adj harris	USPAT;	2002/09/19
		•	US-PGPUB;	13:57
			EPO; JPO;	. 3.3.
			DERWENT;	
			IBM_TDB	
_	322	(harris adj harris) and nano	USPAT;	2002/09/19
		and individual individ	US-PGPUB;	13:59
			EPO; JPO;	13133
			DERWENT;	
	L <u>.</u>		IBM_TDB	

			·	
-	3	(harris n ar harris) and nano	USPAT;	2002/09/19
			US-P PUB;	13:59
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	206	L-shap d near spac r	USPAT;	2002/09/19
			US-PGPUB;	14:01
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	8	(L-shaped near spacer) and (insulator or	USPAT;	2002/09/19
		insulating or dielectric) and (polysilicon or	US-PGPUB;	14:03
		poly-silicon) and (liner or oxide) and spacer	EPO; JPO;	
		and sidewall and (interlevel or inter-level or	DERWENT;	
		interlayer or inter-layer)	IBM_TDB	
-	7	((L-shaped near spacer) and (insulator or	USPAT;	2002/09/19
		insulating or dielectric) and (polysilicon or	US-PGPUB;	14:03
		poly-silicon) and (liner or oxide) and spacer	EPO; JPO;	
		and sidewall and (interlevel or inter-level or	DERWENT;	
		interlayer or inter-layer)) and liner	IBM_TDB	
-	7	(((L-shaped near spacer) and (insulator or	USPAT;	2002/09/19
		insulating or dielectric) and (polysilicon or	US-PGPUB;	14:04
		poly-silicon) and (liner or oxide) and spacer	EPO; JPO;	
]	and sidewall and (interlevel or inter-level or	DERWENT;	
		interlayer or inter-layer)) and liner) and	IBM_TDB	
		((insulator or insulating or dielectric) near10	15105	
ļ		substrate)		
_	6	((((L-shaped near spacer) and (insulator or	USPAT;	2002/09/19
		insulating or dielectric) and (polysilicon or	US-PGPUB;	14:05
		poly-silicon) and (liner or oxide) and spacer	EPO; JPO;	14.03
		and sidewall and (interlevel or inter-level or	DERWENT;	
		interlayer or inter-layer)) and liner) and	IBM_TDB	
		((insulator or insulating or dielectric) near10	10111_100	
		substrate)) and ((polysilicon or poly-silicon)		
		near10 (insulating or insulator or dielectric))		
_	6	(((((L-shaped near spacer) and (insulator or	USPAT;	2002/09/19
_		insulating or dielectric) and (polysilicon or	•	
		poly-silicon) and (liner or oxide) and spacer	US-PGPUB;	14:06
		and sidewall and (interlevel or inter-level or	EPO; JPO;	
		interlayer or inter-layer)) and liner) and	DERWENT;	
		((insulator or insulating or dielectric) near10	IBM_TDB	
		substrate)) and ((polysilicon or poly-silicon)		
		near10 (insulating or insulator or		
		dielectric))) and ((polysilicon or poly-silicon)		
		near10 (liner or oxide))		

ſ	_		HCDAT	0000/00/40
•	5	((((((L-shaped near spacer) and (insulator or	USPAT;	2002/09/19
		insulating r di l ctric) and (polysilicon or	US-PGPUB;	14:22
		poly-silic n) and (liner roxide) and spacer	EPO; JPO;	
		and sid wall and (int rievel rinter-l v lor	DERWENT;	
		interlayer or inter-layer)) and lin r) and	IBM_TDB	
		((insulator or insulating or diel ctric) n ar10		
	1	substrate)) and ((polysilicon or poly-silicon)		
		near10 (insulating or insulator or		
		dielectric))) and ((polysilicon or poly-silicon)		{
		near10 (liner or oxide))) and ((spacer or		
		sidewall) near20 (polysilicon or poly-silicon)		
		near20 (liner or oxide))		
-	226091	(insulator or insulating or dielectric) near20	USPAT;	2002/09/19
		substrate	US-PGPUB;	14:23
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	16063	((insulator or insulating or dielectric) near20	USPAT;	2002/09/19
		substrate) and ((polysilicon or poly-silicon)	US-PGPUB;	14:24
		near20 (insulating or insulator or dielectric))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	112	(((insulator or insulating or dielectric)	USPAT;	2002/09/19
	1.2	near20 substrate) and ((polysilicon or	US-PGPUB;	14:25
		poly-silicon) near20 (insulating or insulator	EPO; JPO;	14.25
		, , ,	1	
		or dielectric))) and (liner near20 (polysilicon	DERWENT;	
	0.5	or poly-silicon))	IBM_TDB	0000/00/40
-	25	((((insulator or insulating or dielectric)	USPAT;	2002/09/19
		near20 substrate) and ((polysilicon or	US-PGPUB;	14:28
		poly-silicon) near20 (insulating or insulator	EPO; JPO;	
		or dielectric))) and (liner near20 (polysilicon	DERWENT;	
		or poly-silicon))) and (spacer near20	IBM_TDB	
		(polysilicon or poly-silicon) near20 liner)		
-	7	(((((insulator or insulating or dielectric)	USPAT;	2002/09/19
		near20 substrate) and ((polysilicon or	US-PGPUB;	14:28
		poly-silicon) near20 (insulating or insulator	EPO; JP O;	
		or dielectric))) and (liner near20 (polysilicon	DERWENT;	
		or poly-silicon))) and (spacer near20	IBM_TDB	
		(polysilicon or poly-silicon) near20 liner))		
		and (in: erlevel or inter-level or interlayer or		
		inter-l: yer)		
-	23	((((((insulator or insulating or dielectric)	USPAT;	2002/09/19
		near20 substrate) and ((polysilicon or	US-PGPUB;	14:30
		poly-silicon) near20 (insulating or insulator	EPO; JPO;	
		or dielectric))) and (liner near20 (polysilicon	DERWENT;	
		or poly-silicon))) and (spacer near20	IBM_TDB	
		(polysiticon or polysilicon) near20 liner))	_	
		and ((electric or insulating or insulator)		
		n ar2: [polysilises or poly-silic n))) and		
		(lin r near20 oxidit)		

•	19	((((((insulator or insulating r di lectric)	USPAT;	2002/09/19
		near2 substra . nd ((p lysilic n or	US-PGPUB;	14:31
		poly-silicon) near 0 (insulating rinsulator	EPO; JPO;	
Ī	·	r dielectric))) and (liner near20 (p lysilicon	DERWENT;	
		or p ly-silic n))) and (spac r near20	IBM_TDB	
		(polysilic n r poly-silic n) n ar20 lin r))		
		and ((dielectric or insulating or insulator)		
		near23 (polysiliman or poly-silicon))) and		
		(liner ar oxi:		
	6	((((((i: ulator c saulating or dielectric)	USPAT;	2002/09/19
		near21 substrate, and ((polysilicon or	US-PCPUB;	14:32
		poly-si'icon) near20 (insulating or insulator	EPO; JPO;	
		or die!actric))) ਰਸਤੀ ਼ੁਜ਼ਿਵਾ near20 (polysilicon	DERWENT;	
		or poly-silicon);; - n-1 (spacer near20	IBM_TDB	
		(poly: `icon or ' 'y-rilicon) near20 liner))		
		and ((electr' i sulating or insulator)		
		near2 polysil or poly-silicon))) and		
		(liner par oxide and (liner near oxide		
		near1(angstro.)		
	25	(((((ins lator o instruction or dielectric)	USPAT;	2002/09/19
		near2 substract) and ((polysilicon or	US-PGPUB;	14:33
		poly-s 'con) n	EPO; JPO;	
		or di tric)) iner near20 (polysilicon	DERWENT;	
		or po ilicor.) (spacer near20	IBM_TDB	
		(polys con or / Hicon) near20 liner))		
		and ((electric rinculating or insulator)		
		near2 polys on poly-silicon))		